

Features

- Uses MHCHXM advanced PerfectMOS technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Excellent Low Ciss
- Qualified according to JEDEC criteria

Applications

- Switching application
- Li-battery protection
- DC-DC

Benefits

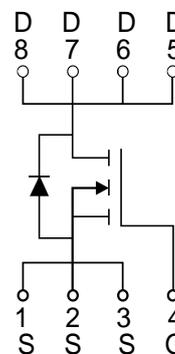
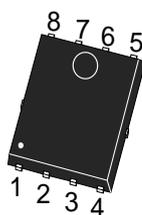
- High robustness and reliability
- Increases maximum current capability
- Low power loss, high power density
- Easy paralleling

Product Summary

V_{DS}	40V
$R_{DS(on)@10V}$ typ	1.12m Ω
I_D	260A



PDFN5060-8L



Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	260	A
Drain Current-Continuous($T_C=100^\circ\text{C}$)	$I_D(100^\circ\text{C})$	210	A
Pulsed Drain Current	I_{DM}	380	A
Maximum Power Dissipation	P_D	200	W
Single pulse avalanche energy	E_{AS}	272	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ\text{C}$

EAS condition : $T_J=25^\circ\text{C}, V_D=32\text{V}, V_G=10\text{V}, L=0.5\text{mH}, R_g=25\Omega, I_{AS}=33\text{A}$

Thermal Characteristic

Parameter	Symbol	Limit	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.4	$^\circ\text{C/W}$



Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.1	1.7	2.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =50A	-	1.12	1.25	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =115A		70	-	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, F=1MHz	-	6200	-	PF
Output Capacitance	C _{oss}		-	2600	-	PF
Reverse Transfer Capacitance	C _{rss}		-	140	-	PF
Gate resistance	R _g	V _{GS} =0V, f=1MHz	-	2.5		Ω
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, I _D =20A V _{GS} =10V, R _G =1.6Ω	-	30	-	nS
Turn-on Rise Time	t _r		-	42	-	nS
Turn-Off Delay Time	t _{d(off)}		-	80	-	nS
Turn-Off Fall Time	t _f		-	31	-	nS
Total Gate Charge	Q _g	V _{DS} =20V, I _D =20A, V _{GS} =10V	-	125	-	nC
Gate-Source Charge	Q _{gs}		-	30		nC
Gate-Drain Charge	Q _{gd}		-	32		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =50A	-		1.2	V
Diode Forward Current	I _S		-	-	260	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =20A di/dt = 100A/μs	-	99	-	nS
Reverse Recovery Charge	Q _{rr}		-	62	-	nC



Typical Electrical and Thermal Characteristics

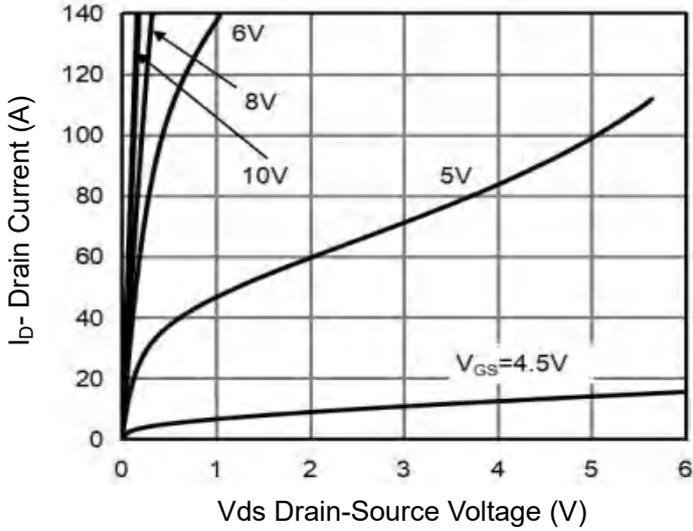


Figure 1 Output Characteristics

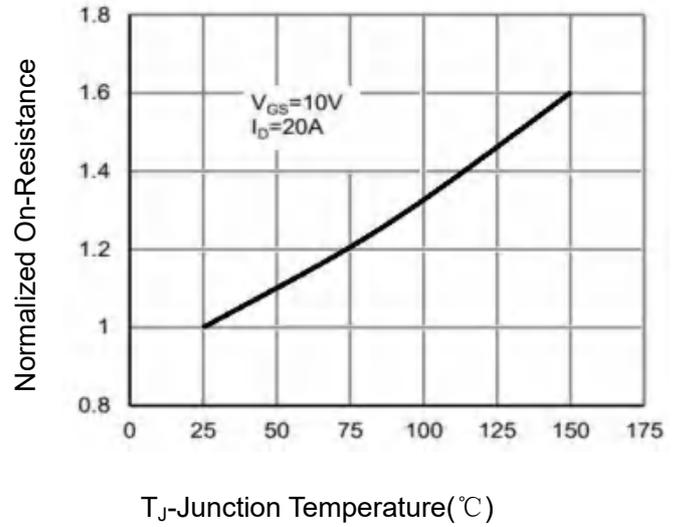


Figure 4 R_{dson} -Junction Temperature

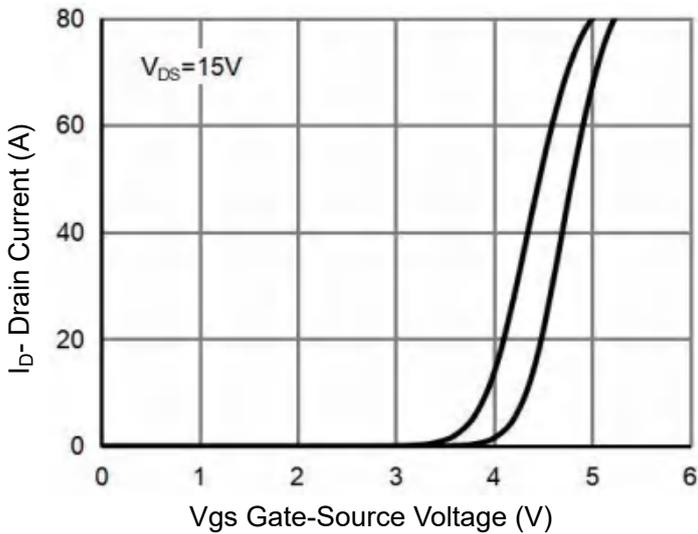


Figure 2 Transfer Characteristics

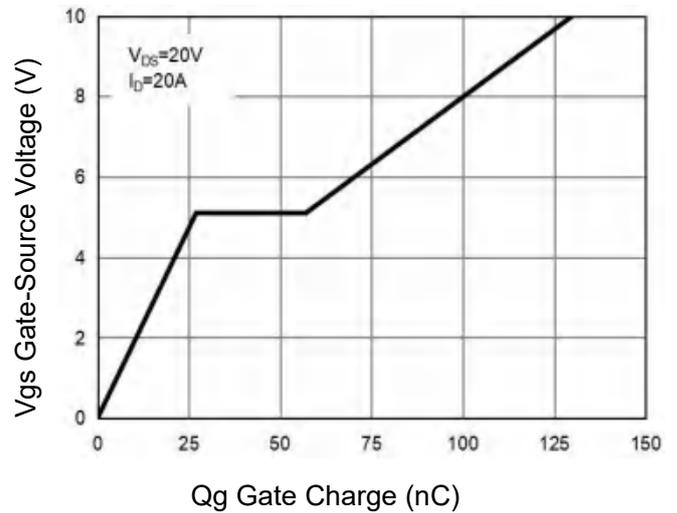


Figure 5 Gate Charge

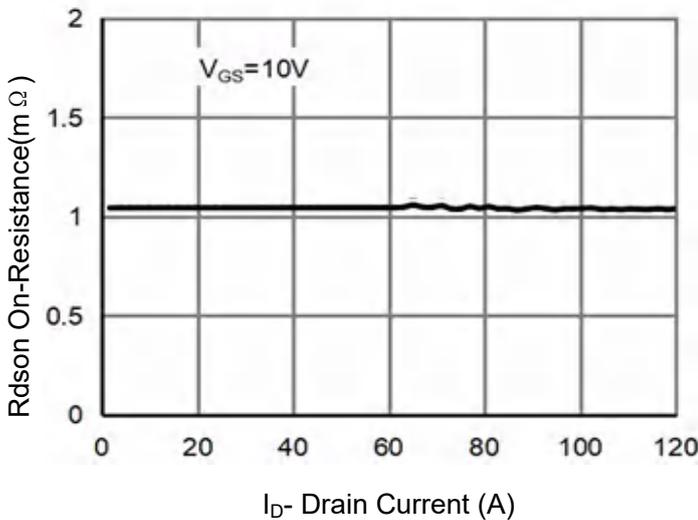


Figure 3 R_{dson} - Drain Current

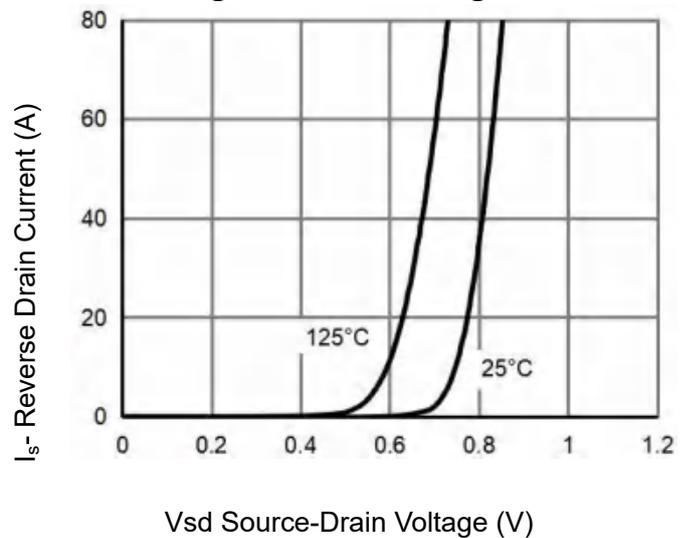


Figure 6 Source- Drain Diode Forward



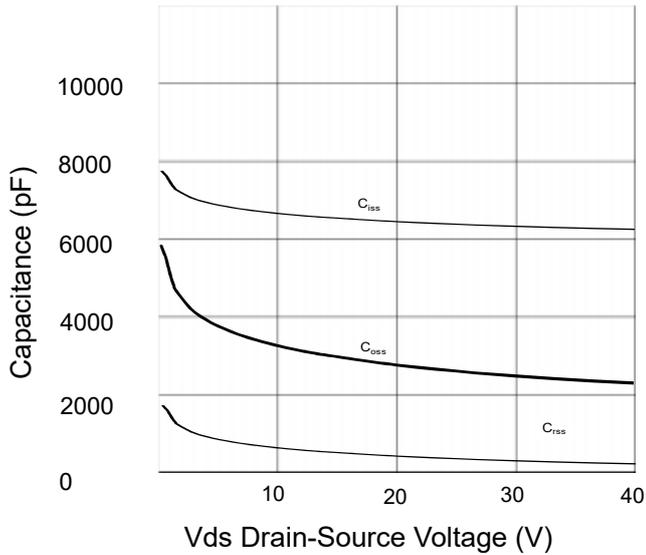


Figure 7 Capacitance vs Vds

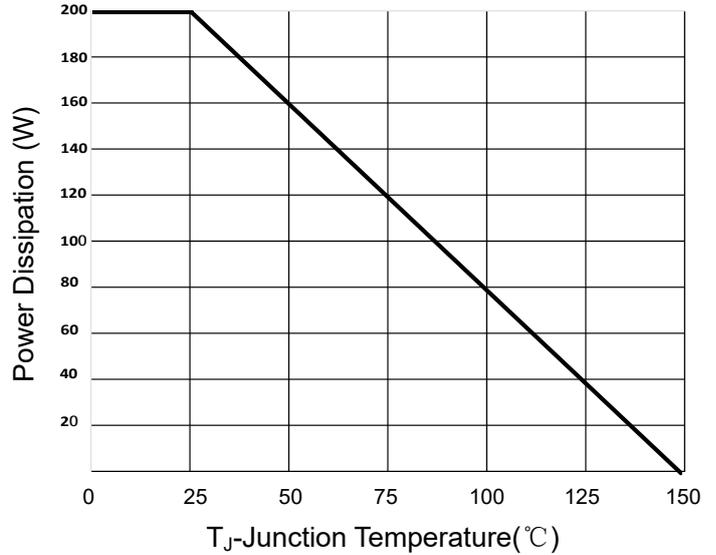


Figure 9 Power De-rating

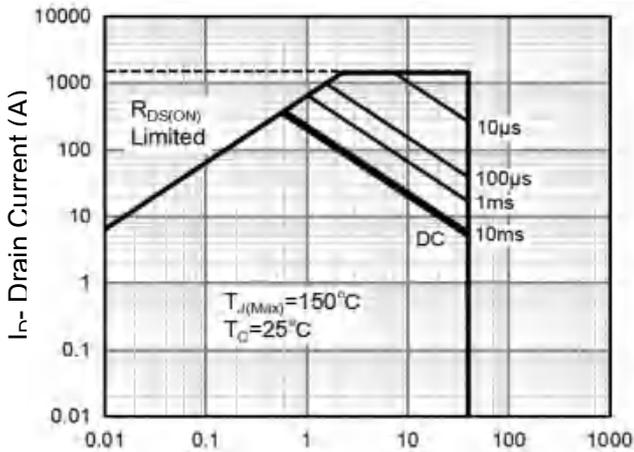


Figure 8 Safe Operation Area

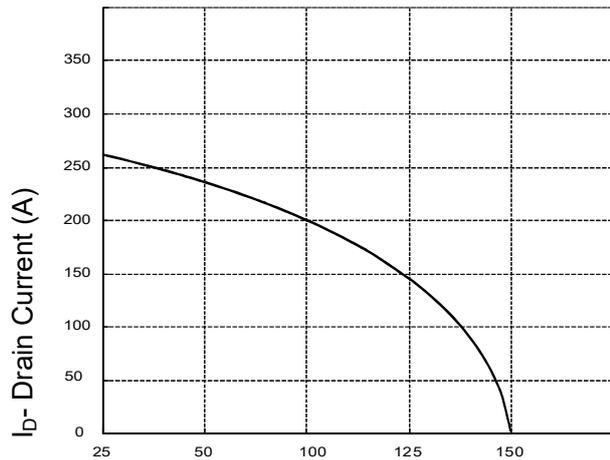


Figure 10 Current De-rating

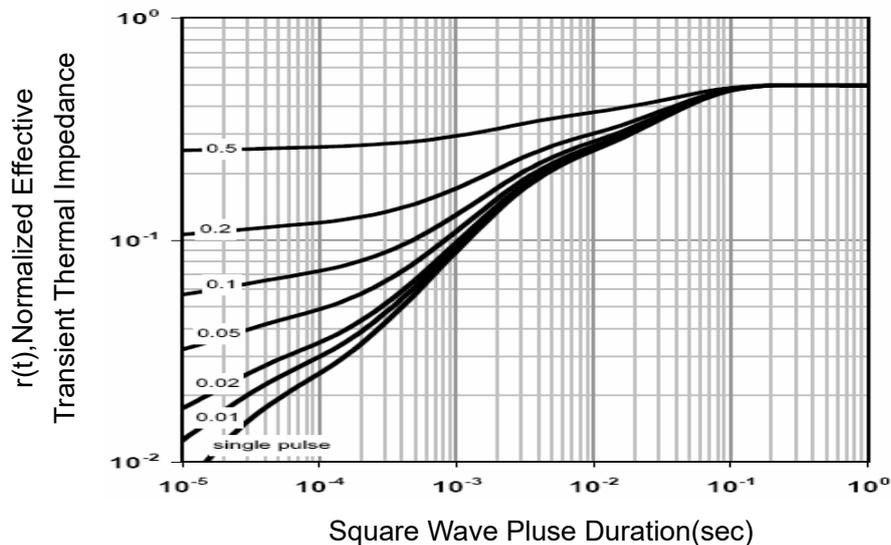
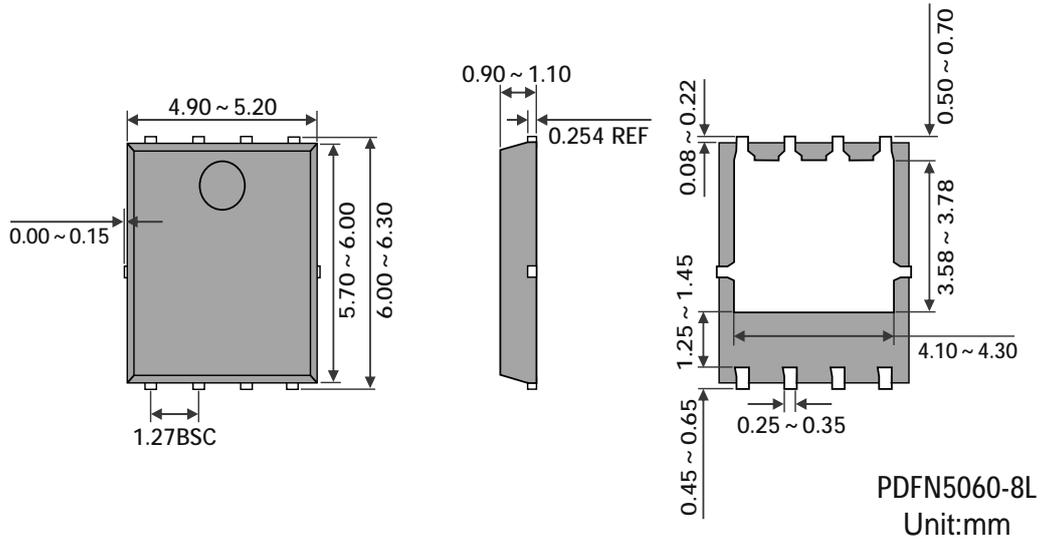


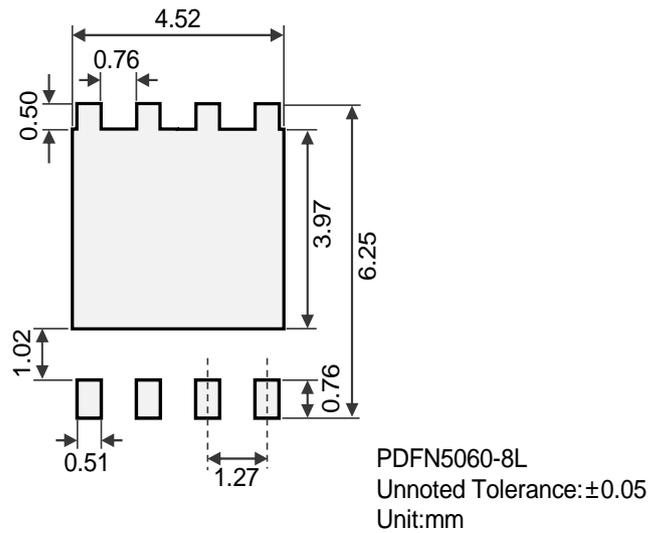
Figure 11 Normalized Maximum Transient Thermal Impedance



Package Outline Dimensions



Suggested Solder Pad Layout



Marking Information

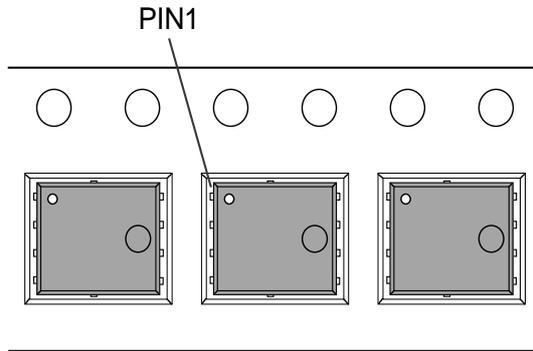


“MHCHXM” = Product Logo
“Marking Code” = The Following
“XXXX” = Date Code Marking

Marking Code	Part Number
S40N12LNA	HXMS40N12LNA



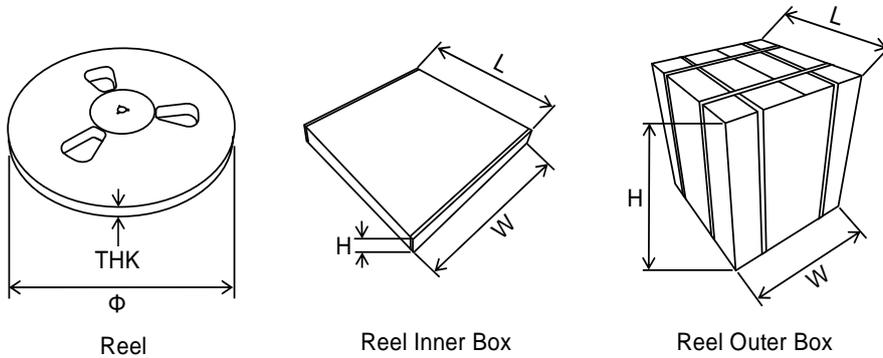
The Orientation Of The Product In The Carrier Tape



Packing Information

Packaging	Part Number	Quantity(pcs)	Size(mm)
Reel	Reel	5000	Φ330×THK15
	Inner Box	10000	L355×W335×H48
	Outer Box	80000	L415×W375×H360

Packaging:Reel



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